

## Physics of Semiconductor Devices (E024641)

Due to Covid 19, the education and evaluation methods may vary from the information displayed in the schedules and course details. Any changes will be communicated on Ufora.

Course size (nominal values; actual values may depend on programme)  
Credits 6.0 Study time 180 h Contact hrs 60.0 h

### Course offerings and teaching methods in academic year 2020-2021

Offering	Language	Location	Teaching Methods	Hours
A (semester 2)	Dutch	Gent	seminar: coached	12.5 h
			exercises	
			microteaching	12.5 h
			practicum	5.0 h
B (semester 2)	English		guided self-study	30.0 h
			seminar: coached	12.5 h
			exercises	
			lecture	30.0 h
			microteaching	12.5 h
			practicum	5.0 h

### Lecturers in academic year 2020-2021

Bakeroot, Benoit	TW06	lecturer-in-charge
Bauwens, Pieter	TW06	co-lecturer

### Offered in the following programmes in 2020-2021

Programme	crdts	offering
<a href="#">Bridging Programme Master of Science in Engineering Physics</a>	6	B
<a href="#">Master of Science in Electromechanical Engineering (main subject Control Engineering and Automation)</a>	6	B
<a href="#">Master of Science in Electromechanical Engineering (main subject Electrical Power Engineering)</a>	6	B
<a href="#">Master of Science in Electrical Engineering (main subject Electronic Circuits and Systems)</a>	6	B
<a href="#">Master of Science in Electromechanical Engineering (main subject Maritime Engineering)</a>	6	B
<a href="#">Master of Science in Electromechanical Engineering (main subject Mechanical Construction)</a>	6	B
<a href="#">Master of Science in Electromechanical Engineering (main subject Mechanical Energy Engineering)</a>	6	B
<a href="#">European Master of Science in Photonics</a>	6	B
<a href="#">Master of Science in Engineering Physics</a>	6	B
<a href="#">Master of Science in Engineering Physics</a>	6	A

### Teaching languages

Dutch, English

### Keywords

semiconductor devices, diode, heterostructures, metal-oxide-semiconductor (MOS) structures, MOS field effect transistor (MOSFET), bipolar transistor, memory devices, solar cells

### Position of the course

The goal of this course is to gain insight in the working principles of semiconductor devices which form the foundation of electronics. We start with an overview of semiconductor physics, after which we treat the basic building blocks (diode, metal-(insulator)-semiconductor) and the basic semiconductor processing steps. In a second part, the most important semiconductor devices (MOSFETs, bipolar transistors,

memory devices...) are treated - including modern variations. Furthermore, this course aims to critically assess papers in the scientific literature and to be able to self-study other semiconductor devices.

## Contents

- Additions to semiconductor physics
- Advanced study of p-n junction diodes including heterojunctions
- The metal-semiconductor structure
- The metal-insulator-semiconductor structure
- Overview of the technology of semiconductor devices
- Metal-oxide-semiconductor field-effect transistors (MOSFETs)
- Bipolar transistors including heterostructures
- Charge coupled devices
- Semiconductor memory devices
- Solar cells
- A special component: thorough self-study of a semiconductor device

## Initial competences

Basic electromagnetism, basic solid-state physics and basic electrical circuits and networks.

## Final competences

- 1 Thorough insight in the working principles of the building blocks (diodes, metal-semiconductor, and metal-insulator-semiconductor structures) of semiconductor devices: equilibrium, DC, AC, and large signal behavior.
- 2 Insight in the operation (equilibrium, DC, AC, and large signal) of the basic semiconductor devices: the MOSFET and the bipolar transistor including modern structures.
- 3 Recognise the most important process steps used in semiconductor device technology.
- 4 Analysing semiconductor devices: drawing band diagrams, assessing IV, CV characteristics, and switching behavior, comparing competing semiconductor devices.
- 5 Critical assessment of articles from scientific literature discussing semiconductor devices.

## Conditions for credit contract

Access to this course unit via a credit contract is determined after successful competences assessment

## Conditions for exam contract

This course unit cannot be taken via an exam contract

## Teaching methods

Guided self-study, lecture, microteaching, practicum, seminar: coached exercises

## Extra information on the teaching methods

The microteaching is done in groups of 2 to 3 students. The purpose is to study an article from recent scientific literature on a semiconductor device and to present the topic to the peers. One student lecture takes about 20 to 30 minutes, followed by a question & answer session of about 10 to 15 minutes.

## Learning materials and price

Lecture notes (English) and handouts PowerPoint presentations (on the electronic learning platform)

## References

- S.M. SZE and Kwok K. Ng, Physics of semiconductor devices, 3rd. ed., John Wiley & Sons, 2007.
- S.M. Sze and M.K. Lee, Semiconductor Devices - Physics and Technology, 3rd. ed., Wiley & Sons, 2013.
- Richard S. Muller and Theodore I. Kamins, Device Electronics for Integrated Circuits, 3rd ed., John Wiley and Sons, 2003.
- Yuan Taur and Tak H. Ning, Fundamentals of Modern VLSI Devices, 2nd ed., Cambridge University Press, 2013.

## Course content-related study coaching

## Evaluation methods

end-of-term evaluation and continuous assessment

## Examination methods in case of periodic evaluation during the first examination period

Open book examination, oral examination

Examination methods in case of periodic evaluation during the second examination period

Open book examination, oral examination

Examination methods in case of permanent evaluation

Participation, assignment, peer assessment, report

Possibilities of retake in case of permanent evaluation

examination during the second examination period is possible in modified form

Extra information on the examination methods

During examination period: Two exams: 1. Theory: oral closed-book exam, written preparation; 2. Exercises: written open-book exam.

Continuous assessment: 1. evaluation of lab work; 2. Evaluation of the microteaching (also peer-evaluation with required participation). Resit examination period: the lab work cannot be redone; there is an alternative possible for the microteaching.

Frequency: From week 7: 1 lab work in two time slots; from then on: the timeslots (i.e. two regular lecture hours) are reserved for student lectures and guest lectures (number of timeslots depends on the number of students).

Calculation of the examination mark

The final mark is determined based on the following weighting coefficients: theory + exercises = 2/3; lab work + microteaching = 1/3. The score on the lab work is transferred to the resit examination period, the score on the microteaching is transferred if the score is at least 10/20, or it has to be redone in alternative form when the score is below 10/20.